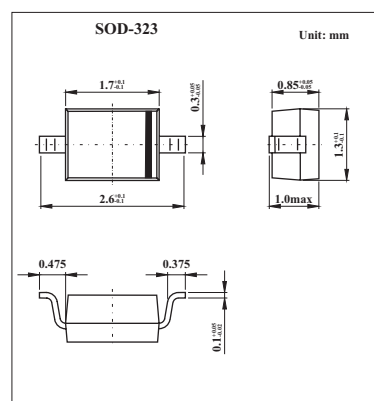


# BAR 63-03W

## ■ Features

- PIN diode for high speed switching of RF signals
- Low forward resistance
- Very low capacitance
- For frequencies up to 3 GHz



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$	50	V
Forward current	$I_F$	100	mA
Total Power dissipation $T_s \leq 111^\circ\text{C}$	$P_{tot}$	250	mW
Operating temperature range	$T_{op}$	-55 to +150	°C
Storage temperature range	$T_{stg}$	-55 to +150	°C
Junction - soldering point <sup>1)</sup>	$R_{thJA}$	$\leq 235$	K/W
Junction-soldering point	$R_{thJS}$	$\leq 155$	K/W

Note:

1.Package mounted on alumina 15mm x 16.7mm x 0.7mm

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_R = 5 \mu\text{A}$	50			V
Reverse current	$I_R$	$V_R = 50\text{V}$			50	nA
Forward voltage	$V_F$	$I_F = 100\text{mA}$		0.95	1.2	V
Diode capacitance	$C_T$	$V_R = 0\text{V}, f = 100\text{MHz}$		0.3		pF
		$V_R = 5\text{V}, f = 1\text{MHz}$		0.21	0.3	
Forward resistance	$r_f$	$I_F = 5\text{mA}, f = 100\text{MHz}$		1.2	2	$\Omega$
		$I_F = 10\text{mA}, f = 100\text{MHz}$		1		
Charge carrier life time	$\tau_{rr}$	$I_F = 10\text{mA}, I_R = 6\text{mA}, I_R = 3\text{mA}$		75		ns
Series inductance	$L_s$			2		nH

## ■ Marking

Marking	G
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